



Features

- Uncooled laser diode with MQW structure
- 9mW CW operation at -40 to +85°C
- High temperature operation without active cooling
- Hermetically sealed active component
- Built-in InGaAs monitor photodiode
- Complies with Telcordia (Bellcore) GR-468-CORE
- Designed for 2.5G high speed optical network
- TO-18 with a 7.5mm A-lens cap

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Optical output power (85°C)	P _O	-	9	mW
LD Forward Current (85°C)	I _{FLD}	-	120	mA
LD Forward Current (25°C)	I _{FLD}	-	100	mA
LD Reverse Voltage (-40~85°C)	V _{RLD}	-	2	V
PD Reverse Voltage (-40~85°C)	V _{RPD}	-	10	V
PD Forward Current (-40~85°C)	I _{FPD}	-	2	mA
Operating Temperature	T _{opr}	-40	85	°C
Storage Temperature	T _{stg}	-40	100	°C

NOTE: Stress level higher than specified value would degrade device performance or reliability significantly

Optical and Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Threshold Current	I _{th}	-	8	-	mA	-40°C, CW
		-	10	14	mA	25°C, CW
		-	30	36	mA	85°C, CW
Slope Efficiency	SE	0.33	0.38	-	mW/mA	25°C, CW, P _o =5mW
		0.19	0.22	-	mW/mA	85°C, CW, P _o =5mW
Optical output power	P _o	9	-	-	mW	CW, kink free
Operating Current	I _{op}	-	-	80	mA	CW, I _{th} +30mA

Forward Voltage	V_F	-	1.2	1.5	V	CW, Po=5mW
Peak Wavelength	λ	1267	1270	1273	nm	CW, Po=5mW
Side Mode Suppression Ratio	Sr	32	35	-	dB	CW, Po=5mW (-40 to 85°C)
$d\lambda/dt$	$d\lambda/dt$	-	0.1	-	nm/°C	
Spectral Width	$\Delta\lambda$	-	-	1	nm	CW, Po=5mW
Rise/Fall Time	tr / tf	-	-	50	ps	Ith+20mA, 20-80%
PD Monitor Current	I_m	100	-	1200	μ A	CW, Po=5mW
PD Dark Current	I_{DARK}	-	-	0.1	μ A	$V_{RPD}=5V$
PD Capacitance	C_t	-	6	15	pF	$V_{RPD}=5V, f=1MHz$
Bandwidth	BW	2.5	-	-	GHz	chip on carrier 85°C, Ith+30mA
Track Error	TE	-1		1	dB	-40°C&85°C
Focal length	FL	7.0	7.5	8.0	mm	Iop=20mA, SMF

Mechanical Drawing

All dimenions in mm

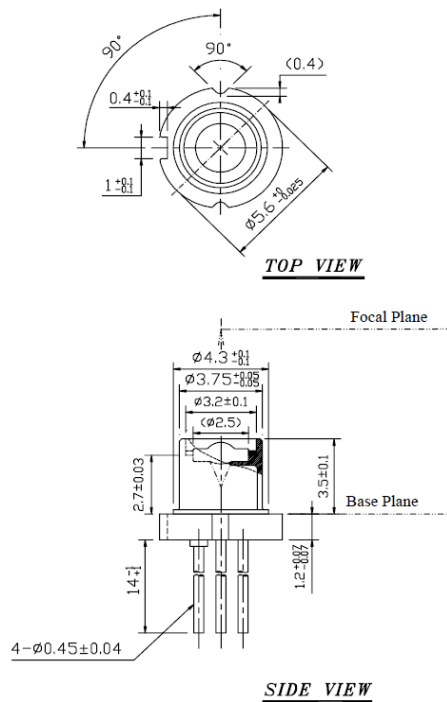


Figure 1 Dimension

PIN Assignment

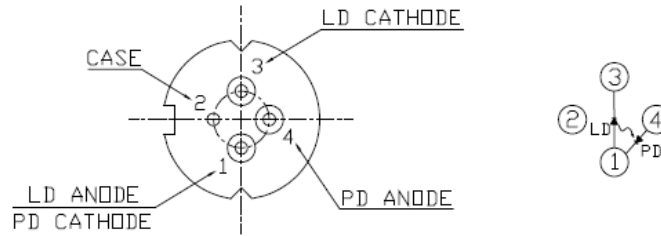


Figure 2 D Type Model PIN Assignment(Bottom View)

Ordering Information

Part No.	Peak Wavelength	Application	Operation Temperature
T-D-TBBC-127DA	1270nm	Designed for 2.5G high speed optical network	-40~85°C

Warnings

Handling Precautions: This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures.

Laser Safety: Radiation emitted by laser devices can be dangerous to human eyes. Avoid eye exposure to direct or indirect radiation.

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Contacts

US Headquarters

8521 Fallbrook Ave, Suite 200
West Hills, CA 91306, USA
Tel: +1(818) 773-9044
Fax: +1(818) 576-9486

China

Building #2&5, West Export Processing
Zone No. 8 Kexin Road, Hi-Tech Zone
Chengdu, 611731, China
Tel: +86-28-8795-8788
Fax: +86-28-8795-8789

Taiwan

9F, No 81, Shui Lee Rd.
Hsinchu, Taiwan R.O.C.
Tel: +886-3-5169222
Fax: +886-3-5169213

www.sourcephotonics.com